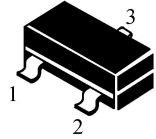




GMA1504

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



■FEATURES 特點

PNP General Purpose Transistor

■MAXIMUM RATINGS (T_a=25°C) 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Collector-Base Voltage 集電極-基極電壓	V _{CBO}	-50	V
Collector-Emitter Voltage 集電極-發射極電壓	V _{CEO}	-50	V
Emitter-Base Voltage 發射極-基極電壓	V _{EBO}	-5	V
Collector Current-Continuous 集電極電流-連續	I _c	-150	mA
Collector Power Dissipation 集電極耗散功率	P _c	225	mW
Junction Temperature 結溫	T _j	150	°C
Storage Temperature Range 儲存溫度	T _{stg}	-55~150	°C

■DEVICE MARKING 打標

GMA1504	O	Y	GR
MARK	ASO	ASY	ASG
H _{FE}	70~140	120~240	200~400

GMA1504

■ELECTRICAL CHARACTERISTICS 電特性

(T_A=25°C unless otherwise noted 如無特殊說明,溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Test Condition 測試條件	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Collector Cutoff Current 集電極截止電流	I _{CBO}	V _{CB} =-50V, I _E =0	—	—	-0.1	μA
Emitter Cutoff Current 發射極截止電流	I _{EBO}	V _{EB} =-5V, I _C =0	—	—	-0.1	μA
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	V _{(BR)CBO}	I _C =-100 μA	-50	—	—	V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	V _{(BR)CEO}	I _C =-1.0mA	-50	—	—	V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓	V _{(BR)EBO}	I _E =-100 μA	-5	—	—	V
DC Current Gain 直流電流增益	H _{FE}	V _{CE} =-6V, I _C =-2mA	70	—	400	—
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	V _{CE(sat)}	I _C =-100mA, I _B =-10mA	—	-0.1	-0.3	V
Base-Emitter Saturation Voltage 基極-發射極飽和壓降	V _{BE(sat)}	I _C =-100mA, I _B =-10mA	—	—	-1.0	V
Noise Figure 噪声係數	NF	V _{CE} =-6V, I _C =-0.1mA, f=1kHz, R _g =10kΩ	—	1.0	10	dB
Transition Frequency 特徵頻率	f _T	V _{CE} =-10V, I _C =-1mA	80	—	—	MHz
Collector Output Capacitance 輸出電容	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz	—	4.0	7.0	pF